

UNITED STATES PATENT AND TRADEMARK OFFICE

UNITED STATES DEPARTMENT OF COMMERCE
United States Patent and Trademark Office
Address: COMMISSIONER FOR PATENTS
P.O. Box 1450
Alexandria, Virginia 22313-1450
www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/718,426	11/20/2003	Karim S. Boutros	PD-200300A (BOE 0463 9643 PA)		
7590 08/15/2005			EXAMINER		
Steven W. Hays			KANG, DONGHEE		
Suite 250 28333 Telegraph Road			ART UNIT	PAPER NUMBER	
Southfield, MI 48034			2811		
			DATE MAILED: 08/15/200:	DATE MAILED: 08/15/2005	

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)
Office Action Summan	10/718,426	BOUTROS ET AL.
Office Action Summary	Examiner	Art Unit
	Donghee Kang	2811
The MAILING DATE of this communication app Period for Reply	ears on the cover sheet with the c	orrespondence address
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply If NO period for reply is specified above, the maximum statutory period w. - Failure to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	66(a). In no event, however, may a reply be time within the statutory minimum of thirty (30) days ill apply and will expire SIX (6) MONTHS from cause the application to become ABANDONE	nely filed s will be considered timely. the mailing date of this communication. O (35 U.S.C. § 133).
Status		
1) Responsive to communication(s) filed on 10 Ju	ne 2005.	
	action is non-final.	
3) Since this application is in condition for allowar closed in accordance with the practice under E	·	
Disposition of Claims		
 4) Claim(s) 1-28 is/are pending in the application. 4a) Of the above claim(s) 9-22 is/are withdrawn 5) Claim(s) is/are allowed. 6) Claim(s) 1-4,6-8 and 23-28 is/are rejected. 7) Claim(s) is/are objected to. 8) Claim(s) are subject to restriction and/or 	from consideration.	
Application Papers		
9) ☐ The specification is objected to by the Examine 10) ☑ The drawing(s) filed on 10 June 2005 is/are: a) Applicant may not request that any objection to the ore Replacement drawing sheet(s) including the correction of the oregin of of t	☑ accepted or b)☐ objected to drawing(s) be held in abeyance. See on is required if the drawing(s) is obj	e 37 CFR 1.85(a). ected to. See 37 CFR 1.121(d).
Priority under 35 U.S.C. § 119		
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority documents 2. Certified copies of the priority documents 3. Copies of the certified copies of the priori	s have been received. s have been received in Applicati ity documents have been receive ı (PCT Rule 17.2(a)).	on No ed in this National Stage
Attachment(s)		
1) Notice of References Cited (PTO-892)	4) Interview Summary	
2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date	Paper No(s)/Mail Da 5) Notice of Informal P 6) Other:	atent Application (PTO-152)

Application/Control Number: 10/718,426 Page 2

Art Unit: 2811

DETAILED ACTION

Drawings

1. The drawings were received on 06-10-05. These drawings are acceptable.

Claim Rejections - 35 USC § 112

- 2. The following is a quotation of the second paragraph of 35 U.S.C. 112:

 The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.
- 3. Claims **23-28** are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

Re claim 23: the limitation "a device formed on one of said at least one layer of said group III-V semiconductor material" is not clear as where the device is positioned in the device. The group III-V semiconductor materials 18 are deposited successively to form the desired device structure. There is no device formed on the group III-V semiconductor materials.

Claims 24-28 are rejected because each includes the limitations of independent claim 23.

The examiner interprets a device formed on one of said at least one layer of group III-V material as a device formed from one of said at least one layer of group III-V material for further prosecution.

Claim Rejections - 35 USC § 102

4. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

Application/Control Number: 10/718,426 Page 3

Art Unit: 2811

A person shall be entitled to a patent unless -

(a) the invention was known or used by others in this country, or patented or described in a printed publication in this or a foreign country, before the invention thereof by the applicant for a patent.

5. Claims **1-4, 6-8 & 23-28** are rejected under 35 U.S.C. 102(a) as being anticipated by Ermer et al. (US 6,380,601).

Re claims 1-2 & 23-24, Ermer et al. teach a semiconductor device comprising (Fig.2):

a germanium substrate (22) having a p-type of doping (28); a nucleating layer (34) of group III-V materials (GalnP) disposed upon said germanium substrate, wherein the deposition of said nucleation layer also forms a germanium junction forming layer (30) on a portion of said germanium substrate (Col.5, lines 8-13) said germanium junction forming layer being actively doped with a constituent element (phosphorus) of said nucleation layer, said actively doped germanium junction forming layer having an opposite doping (n-type) to said first type of doping; at least one layer of a group III-V semiconductor material (36, 42a, 42b.....50) adjacent to and disposed upon said nucleation layer; a first electrical contact (38a) formed on said germanium substrate; a second electrical contact (38b) formed on one of said at least one layer of a group III-V semiconductor material (36); and a third electrical contact (38b') formed on said one of said at least one layer, said third electrical contact electrically coupled to said second electrical contact to form a device, said device selected from the group consisting of transistors, resistors and diodes. See also Col.2, line 53-Col.5, line 17.

Re claims 3-4 & 25-26, Ermer et al. do not explicitly teach said germanium junction forming layer also being actively doped with a second constituent element from

said at least one layer of said group III-V semiconductor material. However, this feature is inherent in Ermer's device because Ermer's device is identical to the claimed structure and both structures are containing same materials (GaAs).

Re claim 6, Ermer et al. teach the level of said first dopant is a function of a desired frequency operating range and photo-response characteristics of the semiconductor device.

Re claims **7-8**, Ermer et al. teach said nucleation layer (InGaP) is lattice-matched to said germanium substrate.

Re claims 27-28, Ermer et al. teach the device further comprising coupling said first electrical contact with said second electrical contact to form an optoelectronic integrated circuit.

Allowable Subject Matter

6. Claim 5 is objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

The following is a statement of reasons for the indication of allowable subject matter: Prior art of record fails to teach or suggest that the device further comprising a fourth electrical contact formed on said one or another of said at least one layer of said group III-V semiconductor material to form a second device.

Response to Arguments

7. Applicant's arguments filed 6-10-05 have been fully considered but they are not persuasive. Applicant argues that Ermer et al. do not teach every features claimed in

Application/Control Number: 10/718,426 Page 5

Art Unit: 2811

independent claims 1 & 23. This is not convincing. Ermer et al. clearly teach substantially the claimed structure. See a statement of rejection for claims 1 & 23.

Conclusion

8. **THIS ACTION IS MADE FINAL.** Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

9. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Donghee Kang whose telephone number is 571-272-1656. The examiner can normally be reached on Monday through Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Steve Loke can be reached on 571-272-1657. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Application/Control Number: 10/718,426

Art Unit: 2811

Page 6

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Donghee Kang Primary Examiner Art Unit 2811

dhk